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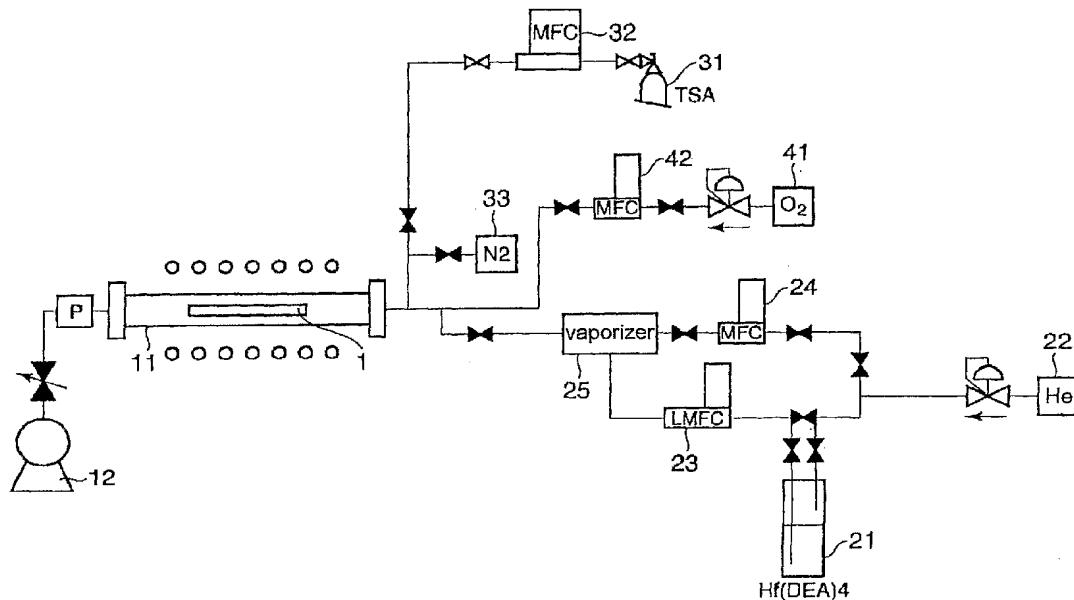
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(54) Title: METHOD FOR FORMING DIELECTRIC OR METALLIC FILMS



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(57) Abstract: Method for producing a metal silicon (oxy)nitride by introducing a carbon-free silicon source (for example,  $(\text{SiH}_3)_3\text{N}$ ), a metal precursor with the general formula  $\text{MX}_n$  (for example,  $\text{Hf}(\text{NEt}_2)_4$ ), and an oxidizing agent (for example,  $\text{O}_2$ ) into a CVD chamber and reacting same at the surface of a substrate.  $\text{MsiN}$ ,  $\text{MSiO}$  and/or  $\text{MSiON}$  films may be obtained. These films are useful as high  $k$  dielectrics films.



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